

List of Publications/Presentations for Stewart W. Wilson

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PUBLICATIONS & PRESENTATIONS:

Medical Applications Using Semiconductor Lasers

Applications of High Power Semiconductor Lasers, San Diego, CA, September 2007

Changing The Landscape Of Aesthetic Technology

Perkin Elmer Technology Leadership Conference, San Jose, CA, January 2007

A High-Power, Broad-Bandwidth 1310nm Superluminescent Diode With Low Spectral Modulation

Photonics West 2006, San Jose, CA

100mW High-Power Depolarized-Superluminescent Diode at 1550nm Wavelength

Photonics West 2006, San Jose, CA

Reliability Testing Methodology of Broadly Tunable Laser Chips for External Cavity Lasers

LEOS Annual Meeting, Tucson, AZ, October 26-30, 2003

High Performance and Highly Functional Semiconductor Optical Amplifiers Based on Hybrid and Monolithic Integration

ECTC 2003, Invited Paper, New Orleans, LA

Reliable High Power 1610nm Free-Space Hermetically Sealed Fabry Perot Single-mode Laser

IMAPS Military, Aerospace, Space and Homeland Security: Packaging Issues and Applications ATW, March 2003, Baltimore, MD

High Power C-Band Semiconductor Booster Optical Amplifier

OFC 2003, 03-C-1573-OFC, Atlanta, GA

High Power External Cavity Semiconductor Laser With Wavelength Tuning Over C,L, and S-bands Using Single-Angled-Facet Gain Chip

CLEO 2002, Post Deadline Paper, CPDB12-1

Early Implementation of SPC at Lasertel

Compound Semiconductor, August 2001, vol 7, #7, pp61-63

Highly efficient individually addressable diode bars for printing applications

Electronic Letters, (SUBMITTED May 2001)

Optimization of High-power Broad-area Semiconductor Lasers

Photonics West, January 2000, San Jose, CA

Reliable High Power GaInAsP/InP (1.9um) Laser Diodes

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Electronic Letters, 1999, **16**, pp1343-1344

High Power Efficient GaInAsP/InP (1.9um) Laser Diode Arrays

Electronic Letters, 1999, **5**, pp397-398

High Power Reliable 1.9um GaInAsP/InP Laser Diode Arrays

16th International Semiconductor Lasers Conference, Oct. 1998, Nara, Japan

High Average Power Density (0.2-0.65 kW/cm²) Diode Laser Stacks For 808nm,915nm & 940nm

16th International Semiconductor Lasers Conference, Oct. 1998, Nara, Japan

Trends & Challenges In The Development Of High-Power Broad-Area Semiconductor Lasers

1998 AFOSR Workshop on Non-linear Optics, Sept 98, Univ. of Arizona

10.9W CW Optical Power From 100um Aperature InGaAs/AlGaAs (915nm) Laser Diode

Electronics Letters, 1998, **22**, pp2126-2127

{7 6 6} Oriented V-Groove Surfaces on Br₂-CH₃OH Etched (1 0 0) GaAs Wafers

Journal of Material Science: Materials in Electronics 1997, **8**, pp109-113